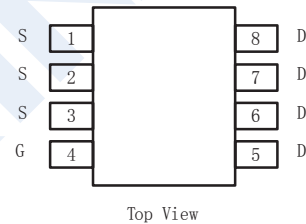
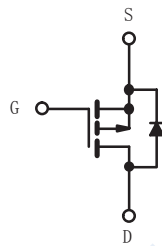
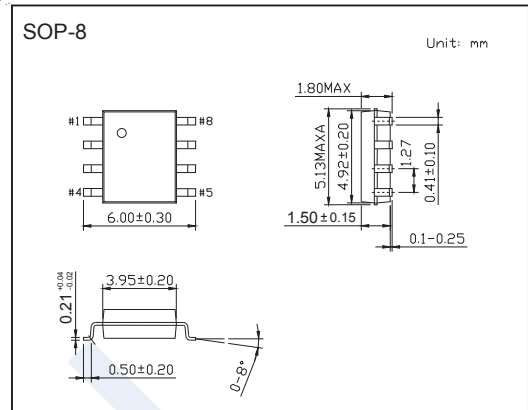


## P-Channel MOSFET

## SI4435DY (KI4435DY)

## ■ Features

- $V_{DS} = -30V$
- $R_{DS(on)} = 0.02 \Omega @ V_{GS} = -10V$
- $R_{DS(on)} = 0.035 \Omega @ V_{GS} = -4.5V$

■ Absolute Maximum Ratings  $T_a = 25^\circ C$ 

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_D$	-8.8	A
Pulsed Drain Current	$I_{DM}$	-50	A
Maximum Power Dissipation	$P_D$	2.5	W
Maximum Junction-to-Ambient	$R_{thJA}$	50	$^\circ C/W$
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to 150	$^\circ C$

## SI4435DY (KI4435DY)

## ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = -250 μA	-30			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V			-1	μA
		V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 70°C			-5	
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA	-1.0	-1.7	-3	V
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±20V			±100	nA
Drain-Source On-State Resistance *	r <sub>DS(on)</sub>	V <sub>GS</sub> = -10V, I <sub>D</sub> = -8.0A		0.015	0.02	Ω
		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -5.0A		0.022	0.035	
On-State Drain Current	I <sub>D(on)</sub>	V <sub>DS</sub> = -5V, V <sub>GS</sub> = -10V	-40			A
Forward Transconductance*	g <sub>fs</sub>	V <sub>DS</sub> = -15V, I <sub>D</sub> = -8A		11		S
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = -15V, V <sub>GS</sub> = -10V, I <sub>D</sub> = -4.6A		47	60	nC
Gate-Source Charge	Q <sub>gs</sub>			7.1		
Gate-Drain Charge	Q <sub>gd</sub>			8		
Turn-On Delay Time	t <sub>d(on)</sub>			16	24	
Rise Time	t <sub>r</sub>	V <sub>DD</sub> = -15V, R <sub>L</sub> = 15 Ω, I <sub>D</sub> = -1A, V <sub>GEN</sub> = -10V, R <sub>G</sub> = 6 Ω		76	110	ns
Turn-Off Delay Time	t <sub>d(off)</sub>			130	200	
Fall Time	t <sub>f</sub>			90	140	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = -2.5A, di/dt = 100A/us		34	51	ns
Continuous Source Current (Diode Conduction)	I <sub>S</sub>			-2.5		A
Diode Forward Voltage*	V <sub>SD</sub>	I <sub>S</sub> = -2.5 A, V <sub>GS</sub> = 0 V			-1.2	V

\* Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.

## ■ Marking

Marking	4435 KC****
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